

General Purpose PNP Epitaxial Planar Transistor

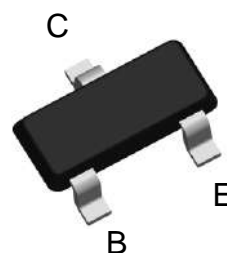
Description

- The KWA1514 is designed for general purpose application requiring high breakdown voltage.
- Large I_C , $I_{C(Max)} = -0.6A$
- High BV_{CEO} , $BV_{CEO} = -160V$
- Complementary to KWC3906.
- Pb-free lead plating and halogen-free package

BV_{CEO}	-160V
I_C	-0.6A
$V_{CESAT(MAX)}$	-0.3V

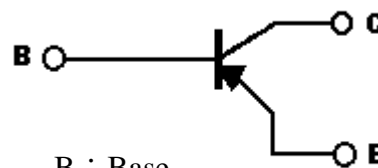
Outline

SOT-23



Symbol

KWA1514



B : Base

C : Collector

E : Emitter

Ordering Information

Device	Package	Shipping
KWA1514	SOT-23 (Pb-free lead plating and halogen-free package)	3000 pcs / tape & reel

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	V _{CB0}	-180	V
Collector-Emitter Voltage	V _{CEO}	-160	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current	I _C	-0.6	A
Power Dissipation	P _D	225	mW
Thermal Resistance, Junction to Ambient	R _{θJA}	556	°C/W
ESD susceptibility		8000 (Note)	V
Operating Junction and Storage Temperature Range	T _j ; T _{stg}	-55~+150	°C

Note : Human body model, 1.5kΩ in series with 100pF

Characteristics (Ta=25°C)

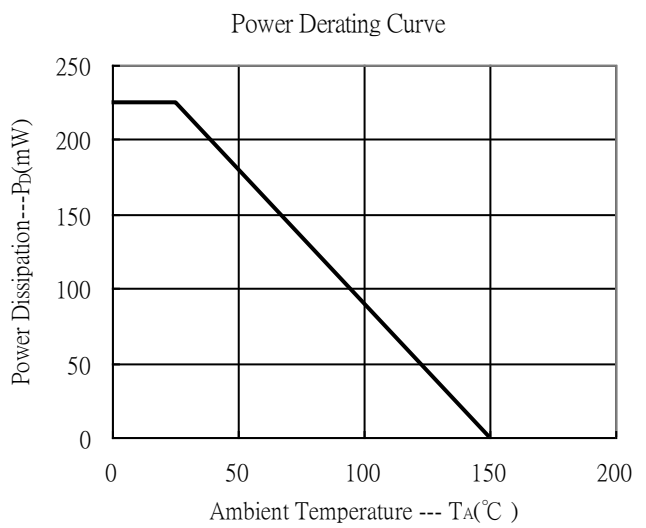
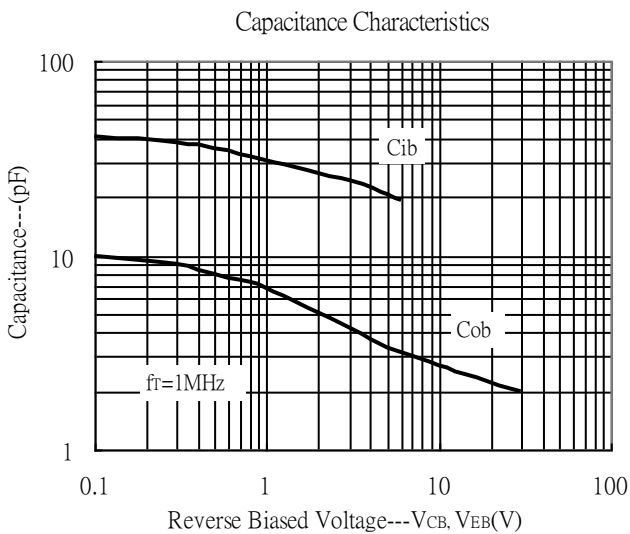
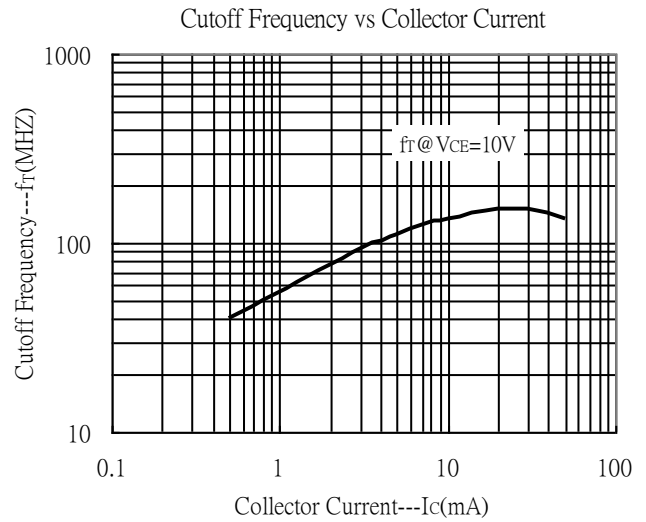
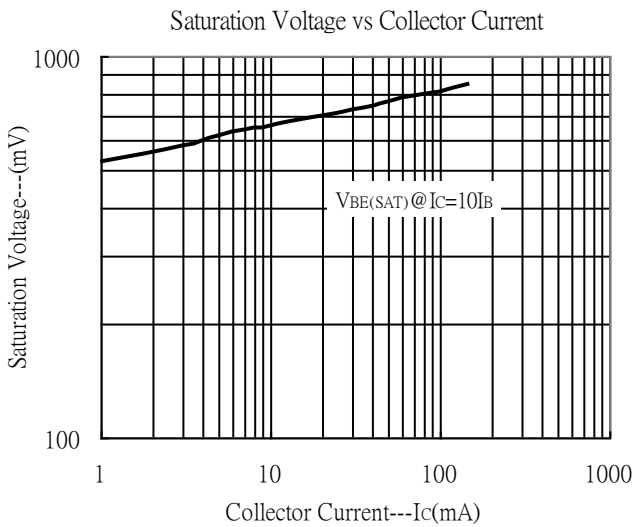
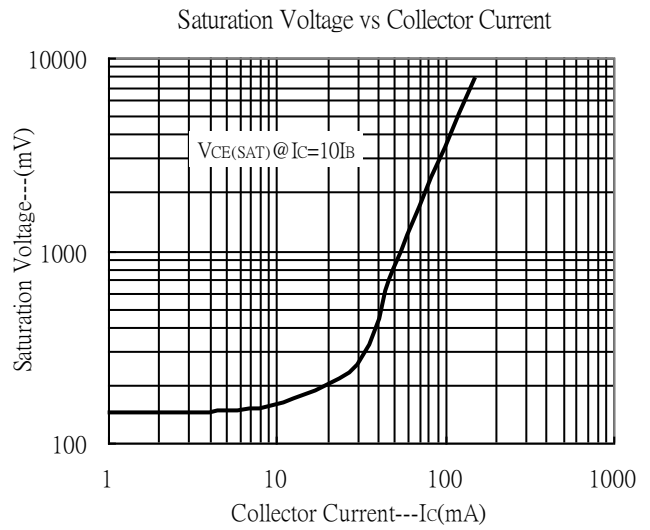
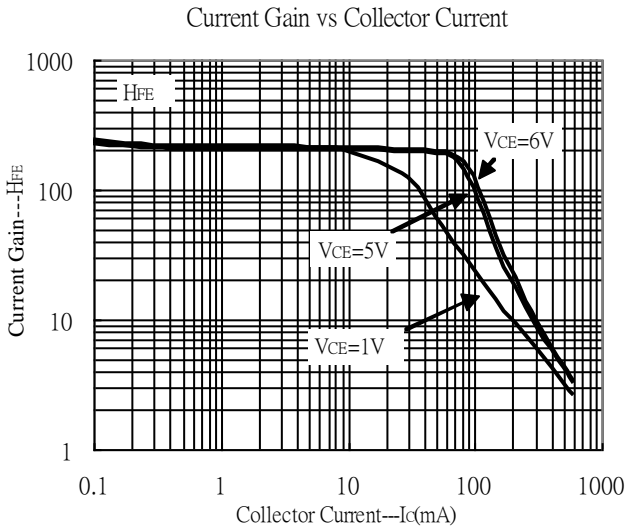
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV _{CB0}	-180	-	-	V	I _C =-50μA
BV _{CEO}	-160	-	-	V	I _C =-1mA
BV _{EBO}	-5	-	-	V	I _E =-50μA
IC _{B0}	-	-	-50	nA	V _{CB} =-120V
IE _{B0}	-	-	-50	nA	V _{EB} =-4V
*V _{CE(sat)} 1	-	0.11	-0.16	V	I _C =-10mA, I _B =-1mA
*V _{CE(sat)} 2	-	0.25	-0.3	V	I _C =-50mA, I _B =-5mA
*V _{BE(sat)} 1	-	-	-1	V	I _C =-10mA, I _B =-1mA
*V _{BE(sat)} 2	-	-	-1	V	I _C =-50mA, I _B =-5mA
h _{FE} 1	100	-	-	-	V _{CE} =-5V, I _C =-1mA
h _{FE} 2	100	-	-	-	V _{CE} =-5V, I _C =-10mA
h _{FE} 3	50	-	-	-	V _{CE} =-5V, I _C =-50mA
h _{FE} 4	120	-	390	-	V _{CE} =-6V, I _C =-2mA
f _T	100	-	-	MHz	V _{CE} =-30V, I _C =-10mA, f=100MHz
C _{ob}	-	-	6	pF	V _{CB} =-10V, f=1MHz

*Pulse Test: Pulse Width ≤380μs, Duty Cycle≤2%

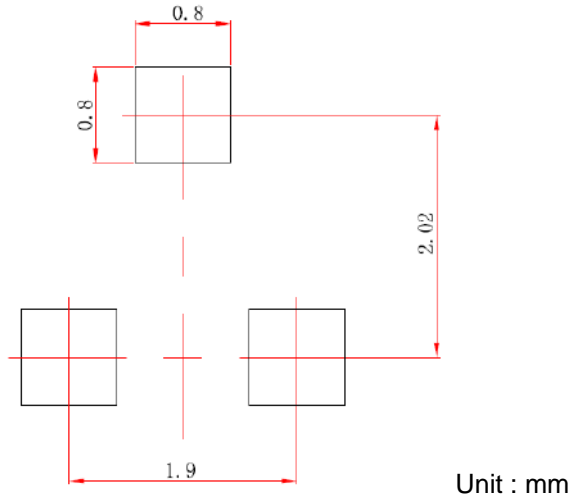
Classification Of h_{FE} 4

Rank	Q	R
Range	120~270	180~390

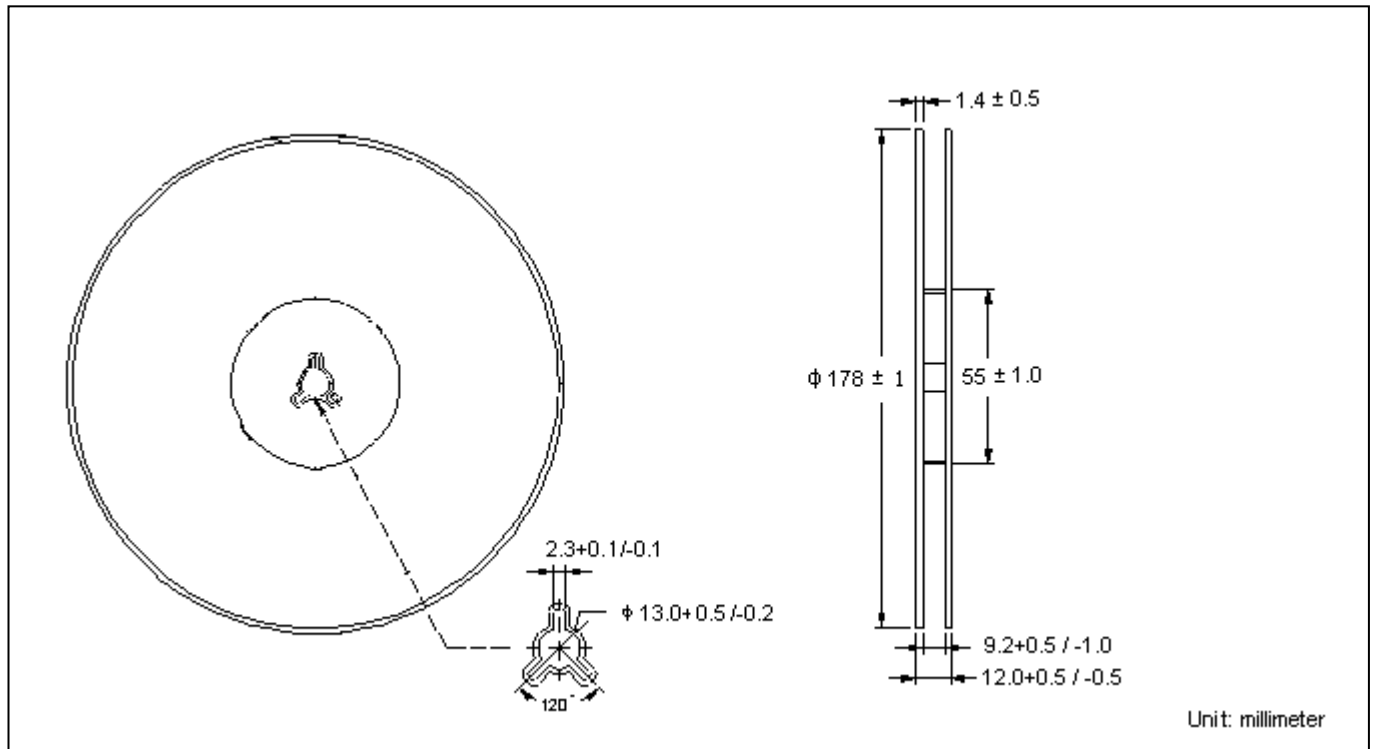
Typical Characteristics



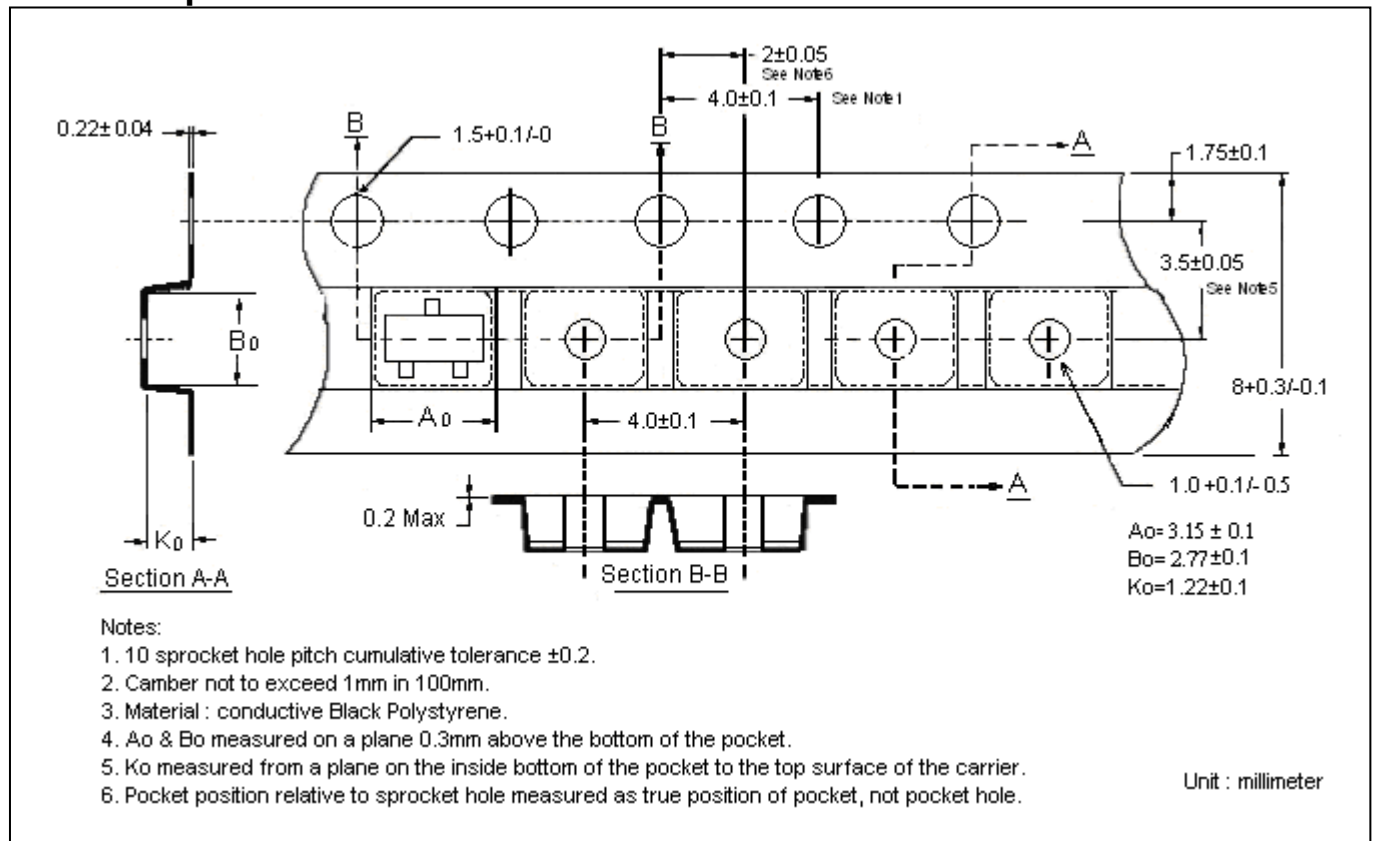
Recommended Soldering Footprint



Reel Dimension



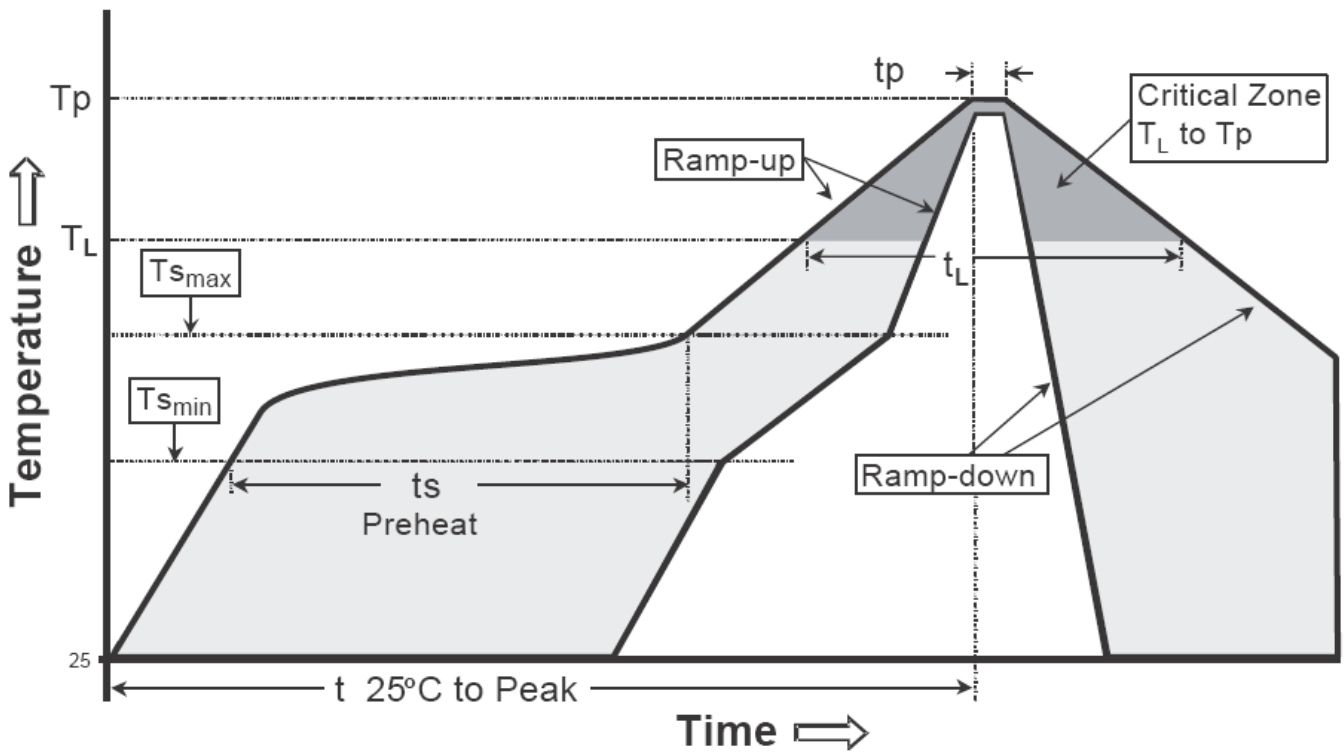
Carrier Tape Dimension



Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

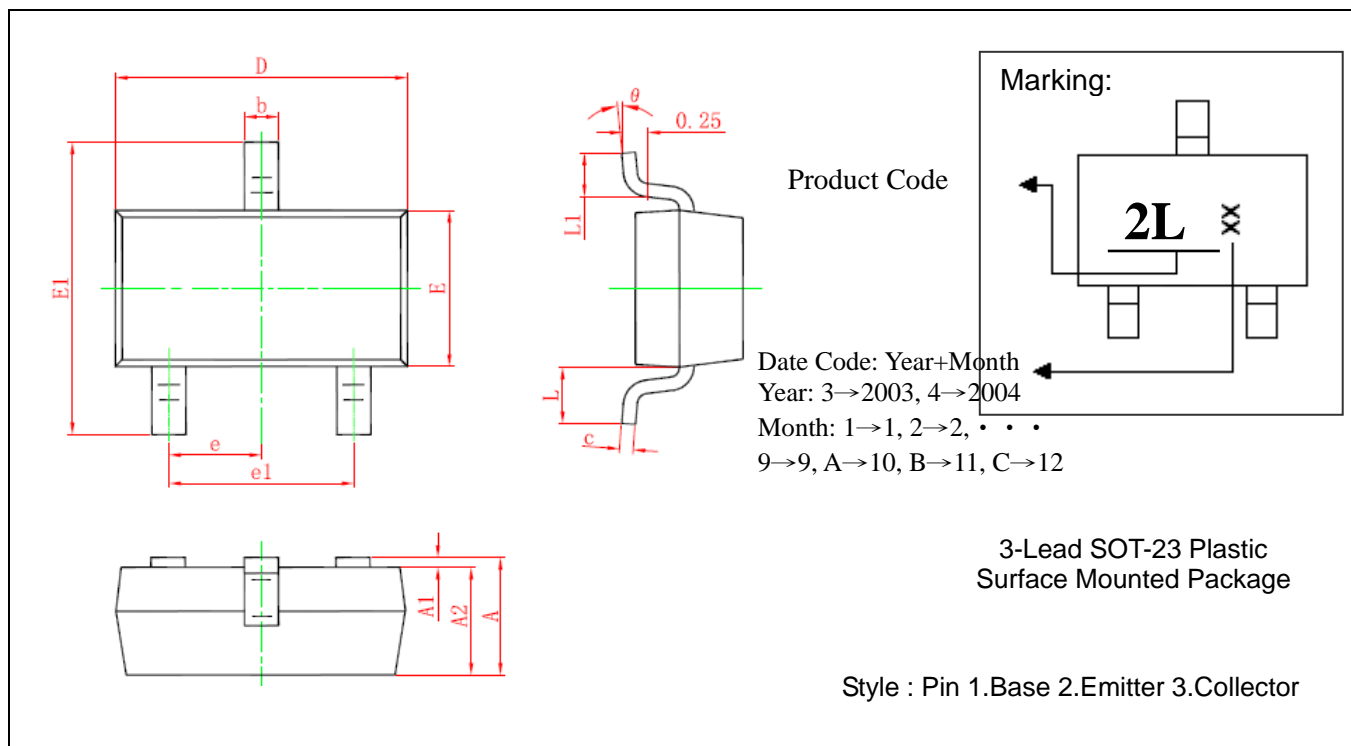
Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (T _{smax} to T _p)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(T _{s min})	100°C	150°C
-Temperature Max(T _{s max})	150°C	200°C
-Time(t _{s min} to t _{s max})	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (T _L)	183°C	217°C
- Time (t _L)	60-150 seconds	60-150 seconds
Peak Temperature(T _p)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

SOT-23 Dimension



Marking:

Product Code

Date Code: Year+Month
 Year: 3→2003, 4→2004
 Month: 1→1, 2→2, . . .
 9→9, A→10, B→11, C→12

3-Lead SOT-23 Plastic Surface Mounted Package

Style : Pin 1.Base 2.Emitter 3.Collector

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.035	0.045	0.900	1.150	E1	0.089	0.100	2.250	2.550
A1	0.000	0.004	0.000	0.100	e	0.037 TYP.		0.950 TYP.	
A2	0.035	0.041	0.900	1.050	e1	0.071	0.079	1.800	2.000
b	0.012	0.020	0.300	0.500	L	0.022 REF.		0.550 REF.	
c	0.003	0.006	0.080	0.150	L1	0.012	0.020	0.300	0.500
D	0.110	0.118	2.800	3.000	θ	0°	8°	0°	8°
E	0.047	0.055	1.200	1.400					

Notes: 1.Controlling dimension: millimeters.
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.

Material:

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0